

RHRPM4424 Gate Driver

STMicroelectronics







A global semiconductor leader

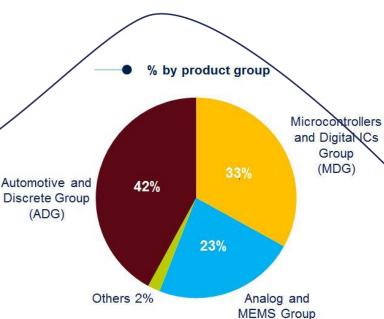


- The largest European semiconductor company
- 2015 revenues of **\$6.9B**
- Approximately 43,200 employees worldwide
- Approximately 8,300 people working in R&D
- 11 manufacturing sites
- Listed on New York Stock Exchange, Euronext Paris and Borsa Italiana, Milano



(AMG)



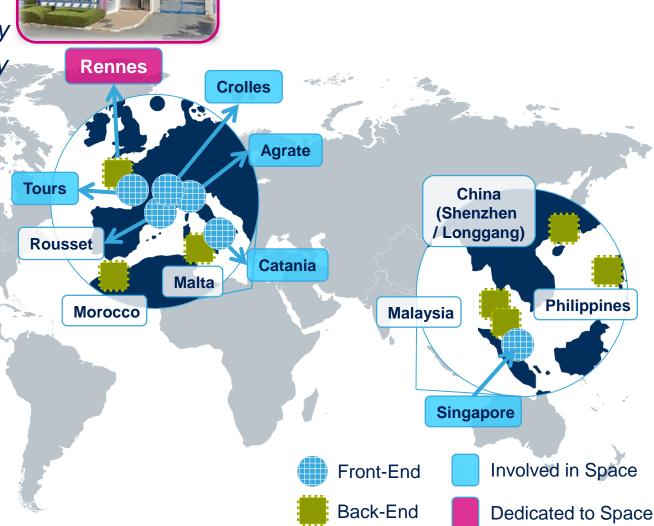


ST Flexible and Independent European Design & Manufacturing

Space certified Since 1979

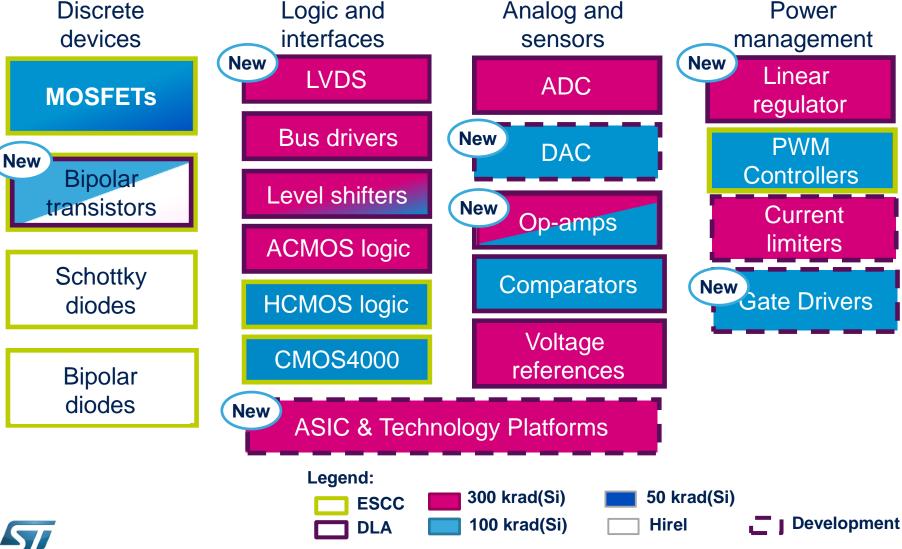
European Space Agency Defense Logistic Agency

- QML & JAN





ESCC / DLA Qualified Product Portfolio 3Q16 Status





RHRPM4424: Key Activities

- Specification with ESA and Users
- Technology Selection
- Design Product Design and Hardenning
- Layout for Radiation Hardness
 - Digital Rad-Hard Library + Analog Hardening by Design
- Process Engineers : Hardening, Reliability
- Product Engineering :
 - Electrical Characterization & Test Program
 - Packaging
 - Qualification Lot Screening Delta ESCC Evaluation
- Radiation Test

Application Support: Data Sheet, Spice Support Support

RHRPM4424 Key Dates

- ITT 08.1QC.20 within ECI3: May 4th, 2009
- Kick off Meeting: Feb 10th, 2010
- Design Start in Catania: June 2011
- First Silicon out : Jan 2012 First Silicon Success
- 2000 Hours Reliability: Dec 2012
- TID: LDR & HDR on 2 wafer lots: Dec 2013
- SEE Test: Feb 2013 + May 2013 + Jul 2014
- Delta ESCC Evaluation Dec 2014
- All Data at DLA: Aug 2016



RHRPM4424: Technology

- BCD6s SOI Selection
 - Bipolar CMOS DMOS : Ideal for Power IC
 - Automotive Qualified: High Quality, Perennity

Volume

- SOI Theoretically Favorable for Radiation
 - Intrisinsic Latch Up Free Low Thickness Oxyde
- Analog Hardening By Design
 - Including with Individual Wells
- Space Specific Reliability Tests Required
 - Temperature and Power Step Stress tests
 - 2000 hour Reliability
 - Activation Energy Recalculation as per Agency Method
 - Technology Vehicle for QML-V Qualification
- Delta ESCC Evaluation

Rad-Hard Low Side MOSFET Drivers

EM: Now

QML: Oct16

KEY FEATURES

• 8 / 9 A sink / source capability

• Vcc : 4.65V to 18V

Power Dissipation: <1.5W @ 70"C

Under Voltage Lock-Out

Separate Power & Signal Ground

Fast Rrise & Fall: 30 ns typ @ CL=4.7nF

In-out delay time: 110ns typ @ CL =10nF

+/- 5ns Matching delay

• Vol = 20 mV @ lout = 1 mA

Low Consumption: 1.8mA max

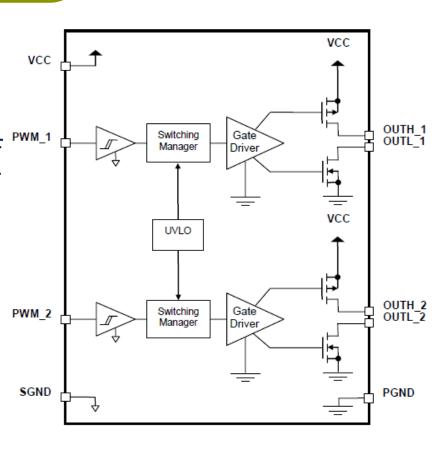
• -55 to +150 °C (Recommended : 125°C)

RADIATION HARDNESS

- 100 krad(Si) ELDRS free (tbc)
- SEL free at 60 Mev.cm2/mg @ 125°C
 - Cross Section 10⁻⁷ cm²

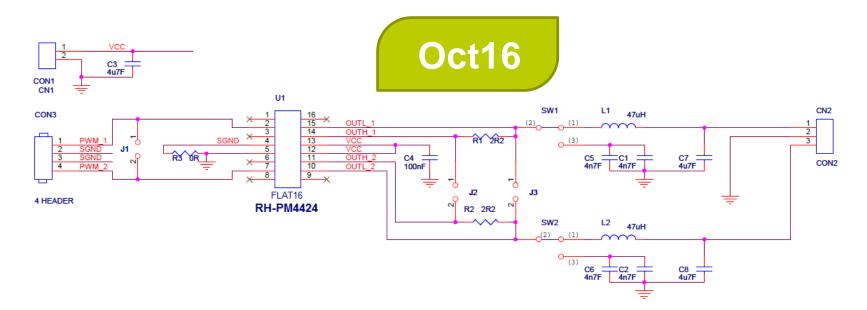
SET Cross Section: 2.10-6 cm2 @ 25°C

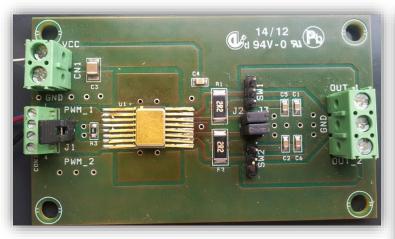
Report Available upon request

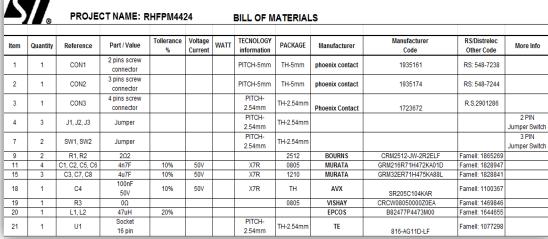


Flat-10 and Flat-16P BCD6s SOI – 30Volt

Application Board

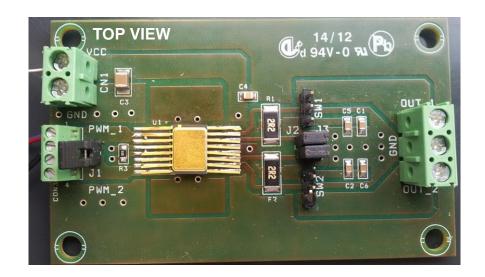


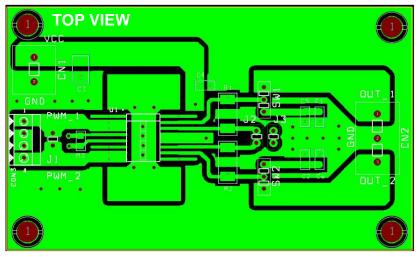


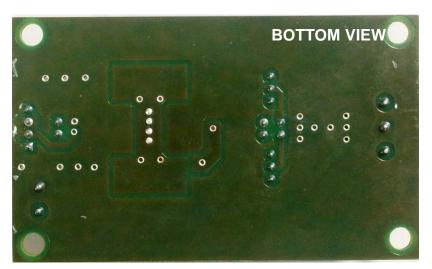


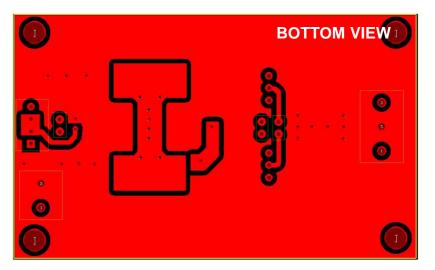


Layout Guidelines for Fastest Design











RHFPM4424 - FLAT28: Application Board & PCB Layout

RHRPM4424 : Next Steps

- Worldwide Promotion
 - Already Selected in Several Application
 - Good Commercial Success Expected
- Series Extension: RHRPM4423
 - Inverting Version
- BCD6s SOI : Proven Rad-Hard Capable
 - Some Rad-Hard Cells to be Added to the Design Kit
 - OTP for Trimming LDMOS Bipolar Transistor...
 - New Rad-Hard Power ICs under Development
 - Integrated Current Limiters (TRP): 90 Volt Version
 - PWM Controller: (TRP): 40V Version
 - High + Low Side Gate Driver (ECI4): 190 Volt Version



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The Ingredients of the Success

- ECI Funding: a Key Enabler or the RHRPM4424
- Specification with the end Customers
 - Customer Survey, Requested by the ITT
- An Industrial Vision
 - Technology: Performance, Quality, Perenity
 - Product Design & Hardening Skills
 - Agency Certified Assembly Infrastructure for Production
 - Technical Support & Sales Network
- The Support of the ESA
 - Power Conversion Team & Radiation Team





Thank you!



